



浙江芯芯电子有限公司
ZHEJIANG XINXIN ELECTIRICAL CO., LTD.

产品规格书

Specification of Products

产品名称：平板型

产品型号：KK1000A

浙江芯芯电子有限公司

ZHEJIANG XINXIN ELECTIRICAL CO., LTD.

地址：浙江省缙云县壶镇镇浙江丽缙五金科技产业园苍山区块内

电话：13857067071

邮编：321404

E-mail:247145749@qq.com

<http://www.zjxxdz1.com>

拟制	审核	核准
丁国盛	李园利	麻伟阳

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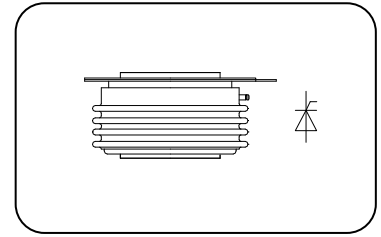
Features

- Interdigitated amplifying gates
- Fast turn-on and high di/dt
- Low switching losses

Typical Applications

- Inductive heating
- Electronic welders
- Self-commutated inverters

$I_{T(AV)}$ **1330A**
 V_{DRM}/V_{RRM} **800~1800V**
 t_q **18~50 μ s**
 I_{TSM} **14 kA**
 I^2t **980 10³A²S**



SYMBOL	CHARACTERISTIC	TEST CONDITIONS	T _j (°C)	VALUE			UNIT
				Min	Type	Max	
I _{T(AV)}	Mean on-state current	180° half sine wave 50Hz Double side cooled,	125			1330	A
						880	
						1000	
V _{DRM} V _{RRM}	Repetitive peak off-state voltage Repetitive peak reverse voltage	V _{DRM} &V _{RRM} , tp=10ms V _{DSM} &V _{RSM} = V _{DRM} &V _{RRM} +100V	125	800		1800	V
I _{DRM} I _{RRM}	Repetitive peak current	V _D = V _{DRM} V _R = V _{RRM}	125			80	mA
I _{TSM}	Surge on-state current	10ms half sine wave	125			14	kA
I ² t	I ² T for fusing coordination	V _R =0.6V _{RRM}				980	A ² s*10 ³
V _{TO}	Threshold voltage		125			1.56	V
r _T	On-state slop resistance					0.33	mΩ
V _{TM}	Peak on-state voltage	I _{TM} =2000A, F=24kN	125			2.22	V
dv/dt	Critical rate of rise of off-state voltage	V _{DM} =0.67V _{DRM}	125			500	V/μs
di/dt	Critical rate of rise of on-state current	V _{DM} = 67%V _{DRM} to 1600A, Gate pulse t _r ≤0.5μs I _{GM} =1.5A	125			1200	A/μs
Q _{rr}	Recovery charge	I _{TM} =1500A, tp=2000μs, di/dt=-60A/μs, V _R =50V	125		750		μC
t _q	Circuit commutated turn-off time	I _{TM} =1000A, tp=1000μs, V _R =50V dv/dt=30V/μs, di/dt=-20A/μs	125	18		50	μs
I _{GT}	Gate trigger current	V _A =12V, I _A =1A	25	40		300	mA
V _{GT}	Gate trigger voltage			0.9		3.0	V
I _H	Holding current			20		500	mA
V _{GD}	Non-trigger gate voltage	V _{DM} =67%V _{DRM}	125	0.3			V
R _{th(j-c)}	Thermal resistance Junction to case	At 180° sine double side cooled Clamping force 24kN				0.020	°C /W
R _{th(c-h)}	Thermal resistance case to heat sink					0.005	
F _m	Mounting force			19		26	kN
T _{stg}	Stored temperature			-40		130	°C
W _i	Weight				440		g
Outline	KT50cT						

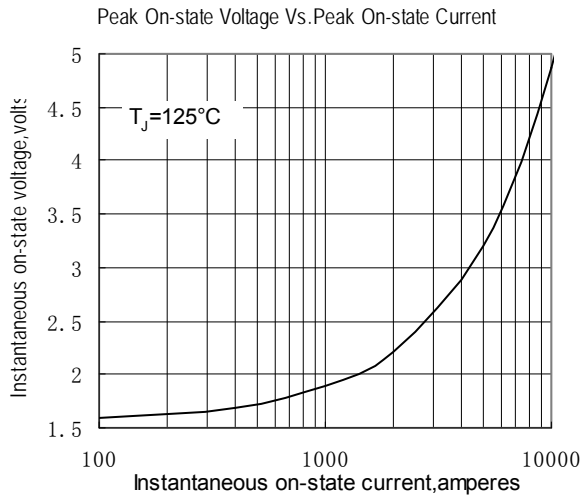


Fig.1

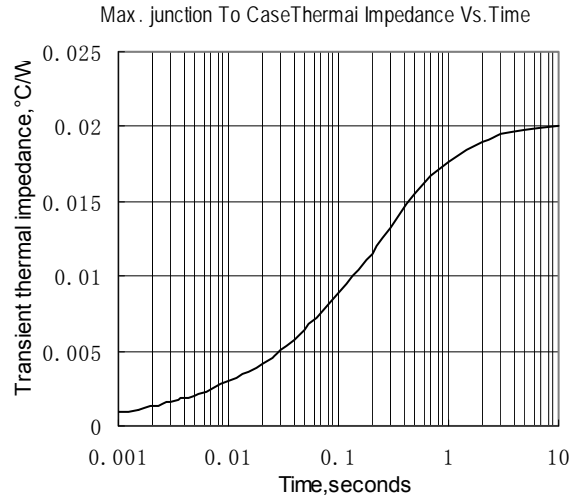


Fig.2

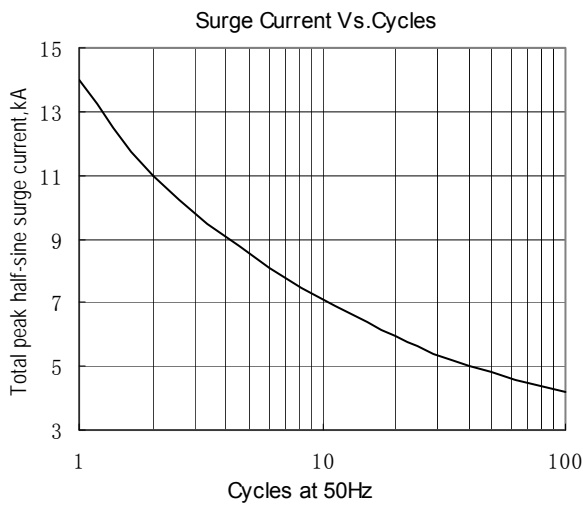


Fig.3

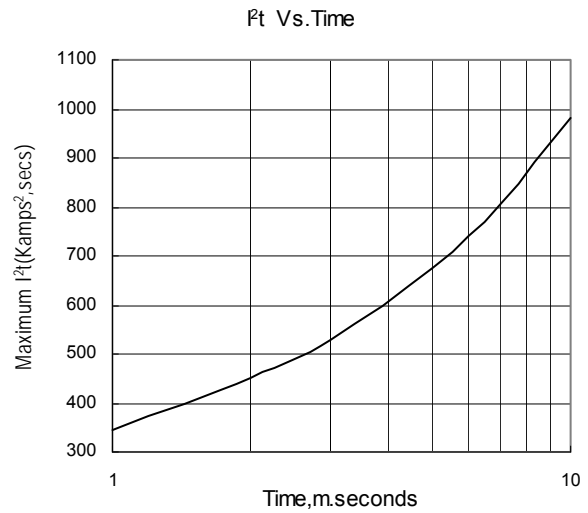


Fig.4

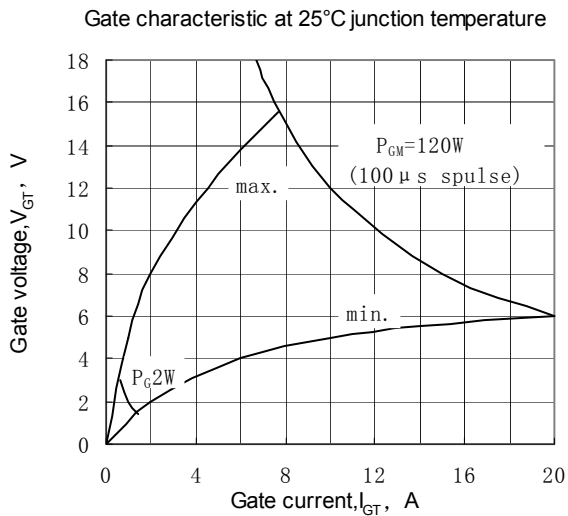


Fig.5

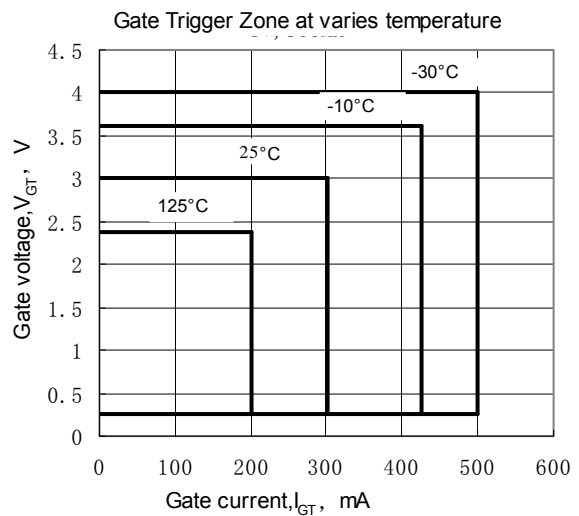


Fig.6

Outline:

